SILICON (Si) POWER MOSFET A CEM3118



CEM3118

30V A 10mΩ A 10.2A A Dual Si MOSFET

SILICON Si MOSFET A SMD type Dual N-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability

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HALOGEN

MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	30V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	I _D	10.2A
Pulsed Drain Current Note 1	I _{DM}	40.8A
Maximum Power Dissipation	PD	2W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	62.5°C/W

APPLICATIONS

Battery	DC/DC	High Side	Low Side	Power
Pack	Converter	Switches	Switches	Banks
+ + -				4

PIN DESCRIPTION

Circuit Diagram	Outline • Top View	Pin No.	Description
$\begin{array}{c} D_{1}(7,8) \\ \hline \\ G_{1}(2) \\ \hline \\ S_{1}(1) \end{array} \qquad \begin{array}{c} D_{2}(5,6) \\ \hline \\ G_{2}(4) \\ \hline \\ S_{2}(3) \end{array}$		1 2 3 4 5 6 7 8	Source MOSFET 1 Gate MOSFET 1 Source MOSFET 2 Gate MOSFET 2 Drain MOSFET 2 Drain MOSFET 2 Drain MOSFET 1 Drain MOSFET 1

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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 250\mu A$	BV _{DSS}	30			V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V$, $I_D = 4A$	R _{DS(ON)}		10	12	mΩ
Static Drain-Source On-Resistance	V_{GS} = 4.5V, I _D = 2A	R _{DS(ON)}		12	16	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	C _{ISS}		735		рF
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	Coss		145		рF
Reverse Transfer Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	C _{RSS}		110		рF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 10A, $R_{G(ext)}$ = 3 Ω	t _{D(ON)}		13		ns
Turn-On Rise Time	V_{DD} = 15V, V_{GS} = 10V, I_D = 10A, $R_{G(ext)}$ = 3 Ω	t _R		7		ns
Turn-Off Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 10A, $R_{\text{G(ext)}}$ = 3 Ω	t _{D(OFF)}		45		ns
Turn-Off Fall Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 10A, $R_{\text{G(ext)}}$ = 3 Ω	t _F		18		ns
Total Gate Charge	V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 10A	Q _G		9.3		nC
Gate Source Charge	$V_{DS} = 15V, V_{GS} = 4.5V, I_D = 10A$	Q _{GS}		1.8		nC
Gate Drain Charge	V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 10A	\mathbf{Q}_{GD}		4.8		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current ^{Note 2}		I _S			1.6	A
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V$, $I_S = 1A$	V_{SD}			1.2	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, t \leq 10 sec

3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4: Guaranteed by design, not subject to production testing.



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Fig. 1 • Output Characteristics Fig. 2 • Transfer Characteristics 64 20 V_{GS}=10,9,8,4V 25°C ID, Drain Current (A) ID, Drain Current (A) 48 15 32 10 T_J=1<u>25[°]℃</u> V_{GS}=3V 16 5 -55 C 0 0 2 3 4 5 0 1 0 2 3 4 5 1 VDS, Drain-to-Source Voltage (V) VGS, Gate-to-Source Voltage (V) Fig. 3 • Capacitance Fig. 4 - On-Resistance Variation with Temperature 2.2 1050 I_D=4A RDS(ON), On-Resistance(Ohms) V_{GS}=10V 900 1.9 RDS(ON), Normalized C, Capacitance (pF) Ciss 750 1.6 600 1.3 450 1.0 300 Coss 0.7 150 C_{rss} 0 0.4 6 0 3 9 12 15 -100 -50 0 50 100 150 200 VDS, Drain-to-Source Voltage (V) TJ, Junction Temperature(°C) Fig. 6 - Body Diode Forward Voltage Variation Fig. 5 - Gate Threshold Variation with Temperature with Source Current 1.3 V_{GS}=0V V_{DS}=V_{GS} Gate-Source Threshold Voltage I_D=250μA s, Source-drain current (A) 1.2 VTH, Normalized 1.1 10¹ 1.0 0.9 10⁰ 0.8 0.7 0.6 10^{-1} -25 0 25 50 75 0.3 0.6 0.9 1.2 -50 100 125 150 1.5 1.8 VSD, Body Diode Forward Voltage (V) TJ, Junction Temperature(°C)



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

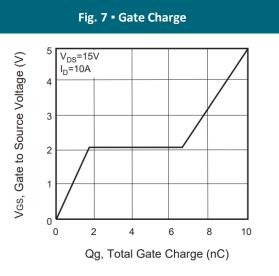


Fig. 9 - Breakdown Voltage Variation vs. Temperature

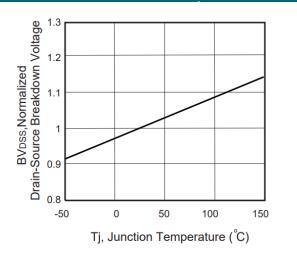
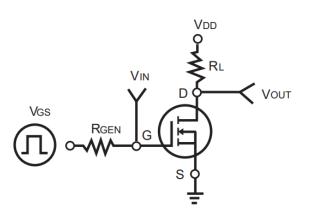


Fig. 10 - Switching Test Circuit



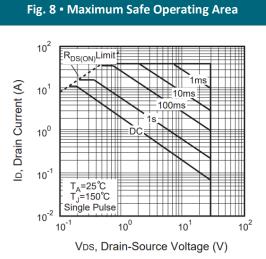
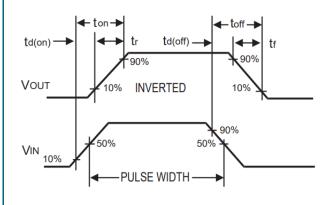


Fig. 11 • Switching Waveforms



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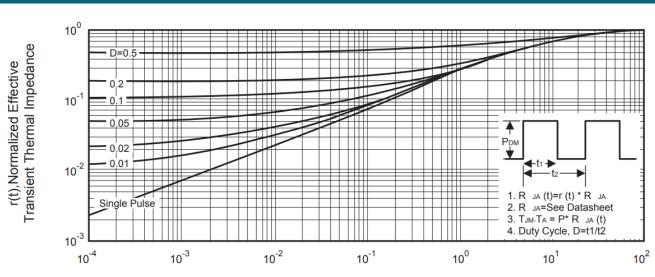
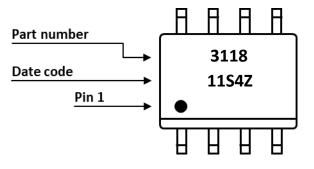


Fig. 12 • Normalized Thermal Transient Impedance Curve

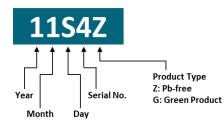
Square Wave Pulse Duration (sec)

PART MARKING



DATE CODE

Example: 11S4Z



1	2	3	4	5	6	7	8	9	Α
01	02	03	04	05	06	07	08	09	10
В	С	D	Ε	F	G	Н		J	К
11	12	13	14	15	16	17	18	19	20
L	Μ	Ν	0	Ρ	Q	R	S	Т	U
21	22	23	24	25	26	27	28	29	30
V									
31									

Coding list for "Day"

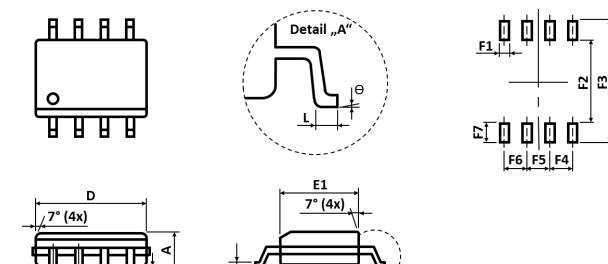
Coding list for "Month"



• Detail "A"



PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Sym	Millimeters	Millimeters	Millimeters	Sym	Millimeters	Millimeters	Millimeters

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	0.500	-	F5	-	1.270	-
F2	-	4.250	-	F6	-	1.270	-
F3	-	6.250	-	F7	-	1.000	-
F4	-	1.270	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

ORDERING INFORMATION

В

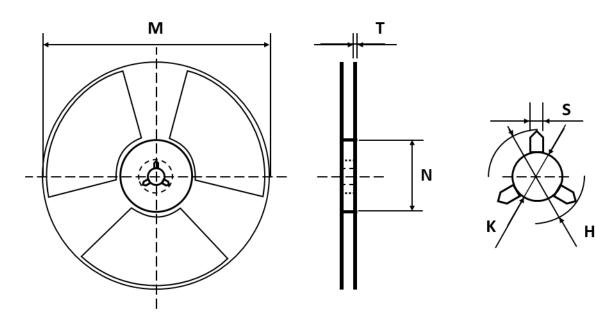
A1

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEM3118	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs	



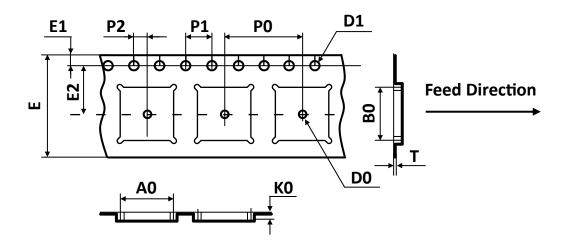


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	9550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

TAPE DIMENSIONS All dimensions in mm



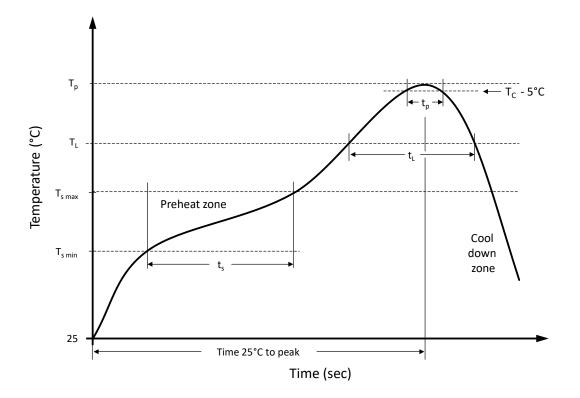
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
509	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
SO8	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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